



Description

The HXY12N65F can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220F, which accords with the RoHS standard.

General Features

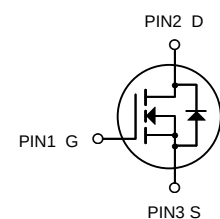
$V_{DS} = 650V, I_D = 12A$
 $R_{DS(ON)} < 0.8 \Omega @ V_{GS} = 10V$

Application

- Power switch circuit of adaptor and charger.



TO-220F



N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Units Tube
HXY12N65F	TO-220F	HXY MOSFET	50

Absolute Maximum Ratings@ $T_J = 25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D @ T_C = 25^\circ C$	Drain Current, $V_{GS} @ 4.5V$	12	A
$I_D @ T_C = 100^\circ C$	Drain Current, $V_{GS} @ 4.5V$	7.5	A
IDM	Pulsed Drain Current ¹	48	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	42	W
E_{AS}	Single Pulse Avalanche Energy ⁴	550	mJ
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$



Electrical Characteristics (Tc= 25℃ unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	650	--	--	V
ΔBV _{DSS} /ΔT _J	Bvdss Temperature Coefficient	I _D =250uA, Reference 25℃	--	0.7	--	V/℃
I _{DSS}	Drain to Source Leakage Current	V _{DS} =650V, V _{GS} = 0V, T _a = 25℃	--	--	1	μA
		V _{DS} =520V, V _{GS} = 0V, T _a = 125℃	--	--	100	μA
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =+30V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} =-30V	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =6A	--	0.67	0.8	Ω
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	--	4.0	V
Pulse width tp ≤ 300μs, δ ≤ 2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g _{fs}	Forward Transconductance	V _{DS} =15V, I _D =6A	--	12	--	S
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz	--	1993	--	pF
C _{oss}	Output Capacitance		--	160	--	
C _{rss}	Reverse Transfer Capacitance		--	9.5	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =12A V _{DD} = 325V R _G =10Ω	--	28	--	ns
t _r	Rise Time		--	26	--	
t _{d(OFF)}	Turn-Off Delay Time		--	64	--	
t _f	Fall Time		--	45	--	
Q _g	Total Gate Charge	I _D =12A V _{DD} =520V V _{GS} = 10V	--	40	--	nC
Q _{gs}	Gate to Source Charge		--	10	--	
Q _{gd}	Gate to Drain ("Miller") Charge		--	14	--	



Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I _S	Continuous Source Current (Body Diode)		--	--	12	A
I _{SM}	Maximum Pulsed Current (Body Diode)		--	--	48	A
V _{SD}	Diode Forward Voltage	I _S =12A, V _{GS} =0V	--	--	1.5	V
trr	Reverse Recovery Time	I _S =12A, T _J = 25℃ dI _F /dt=100A/us, V _{GS} =0V	--	651	--	ns
Qrr	Reverse Recovery Charge		--	4297	--	nC
I _{RRM}	Reverse Recovery Current		--	13.2	--	A
Pulse width tp≤300μs, δ ≤2%						

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	2.98	$^{\circ}C/W$
$R_{\theta JA}$	Junction-to-Ambient	62.5	$^{\circ}C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=10mH, I_D=10.5A$, Start $T_J=25^{\circ}C$

^{a3}: $I_{SD}=12A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}$, Start $T_J=25^{\circ}C$



Characteristics Curve:

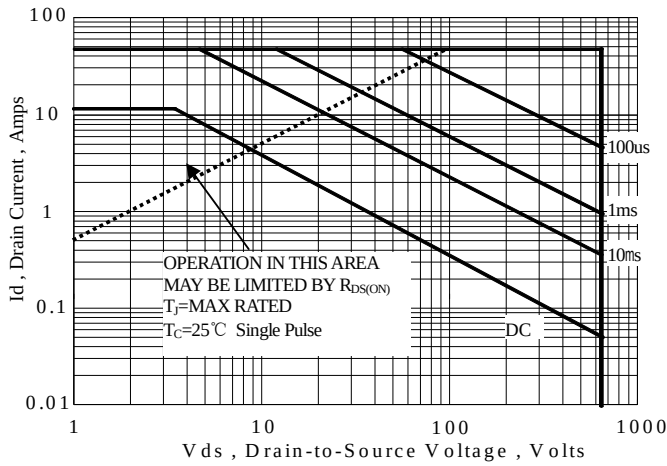


Figure 1 Maximum Forward Bias Safe Operating Area

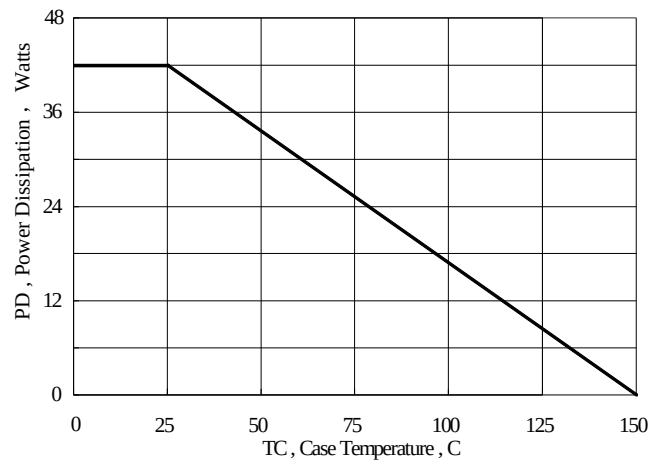


Figure 2 Maximum Power Dissipation vs Case Temperature

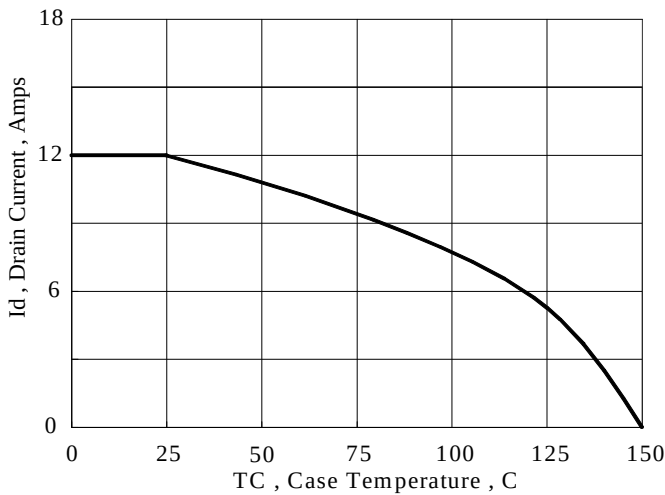


Figure 3 Maximum Continuous Drain Current vs Case Temperature

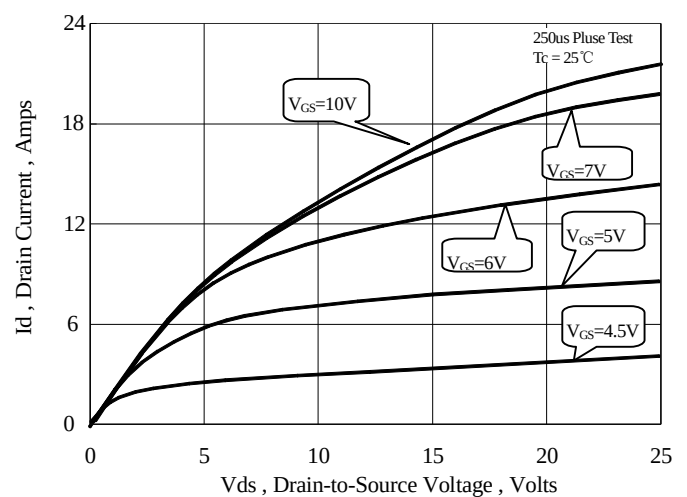


Figure 4 Typical Output Characteristics

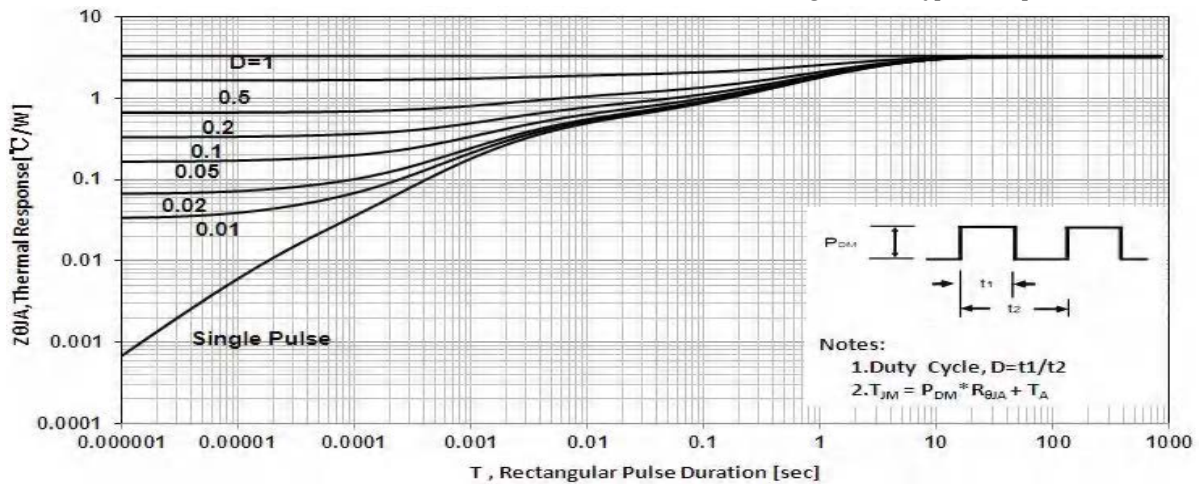


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

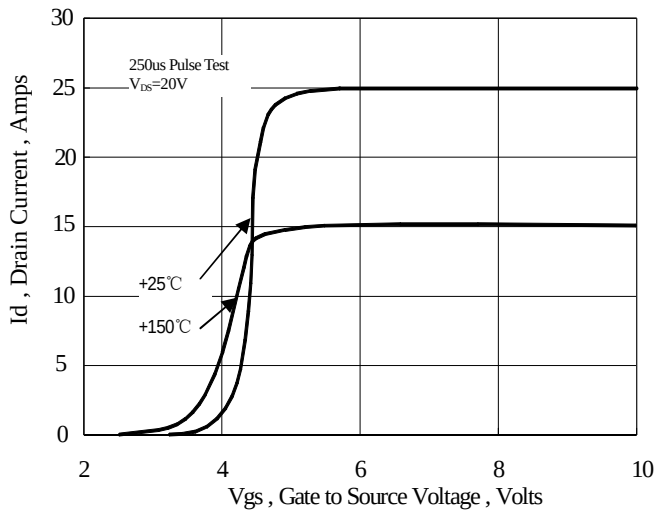


Figure 6 Typical Transfer Characteristics

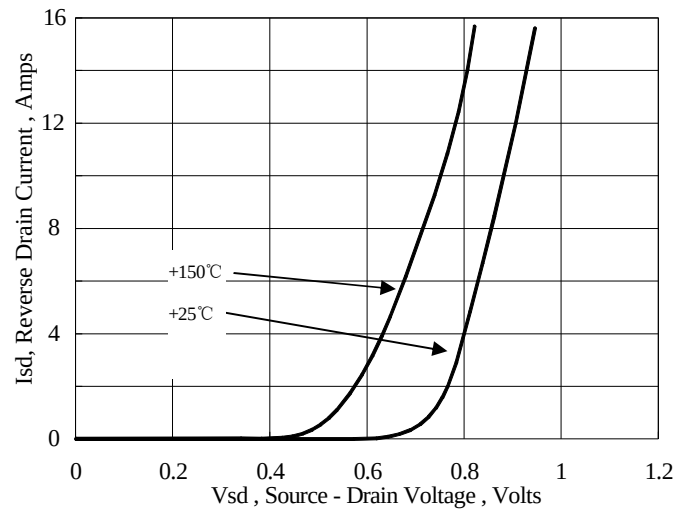


Figure 7 Typical Body Diode Transfer Characteristics

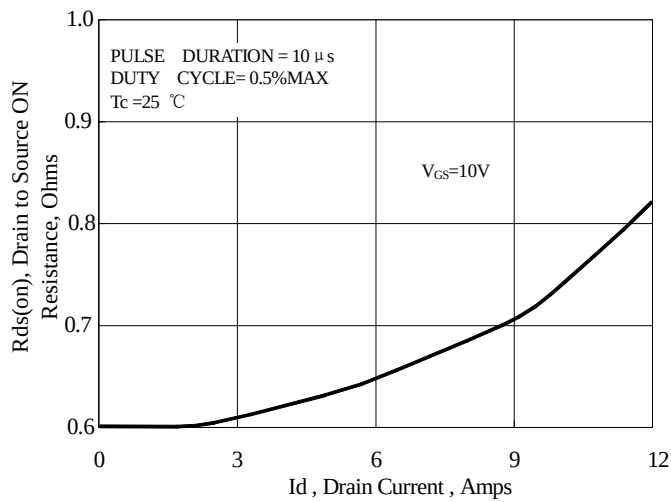


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

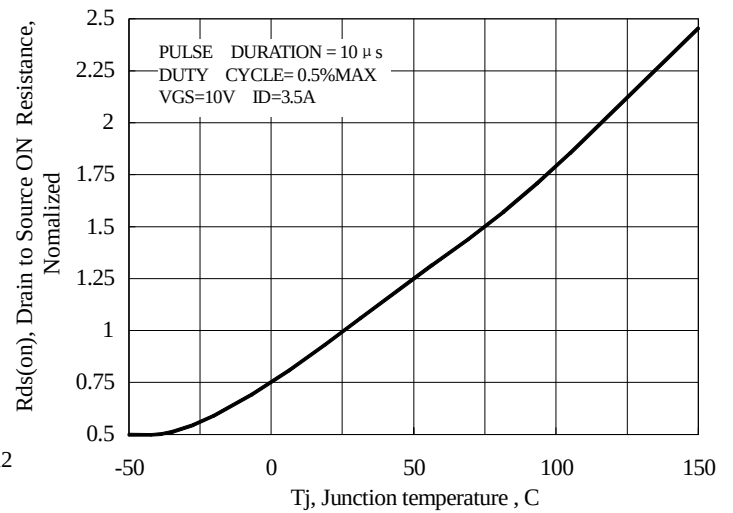


Figure 9 Typical Drain to Source on Resistance vs Junction Temperature

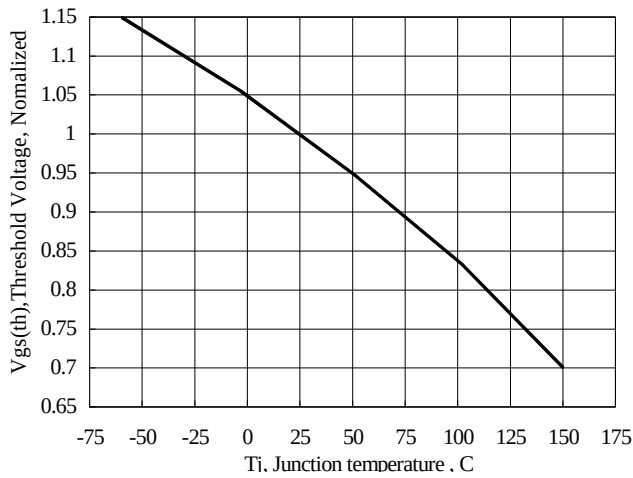


Figure 10 Typical Theshold Voltage vs Junction Temperature

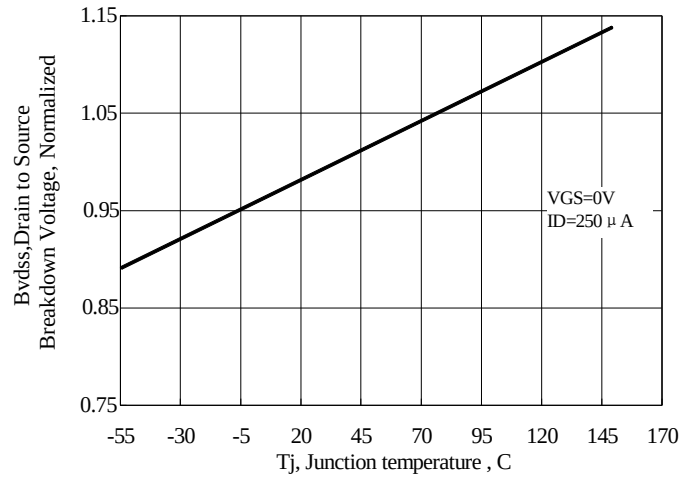


Figure 11 Typical Breakdown Voltage vs Junction Temperature

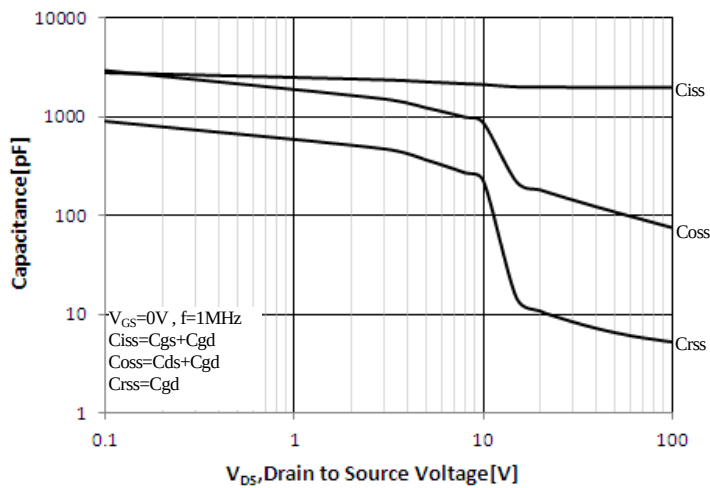


Figure 12 Typical Capacitance vs Drain to Source Voltage

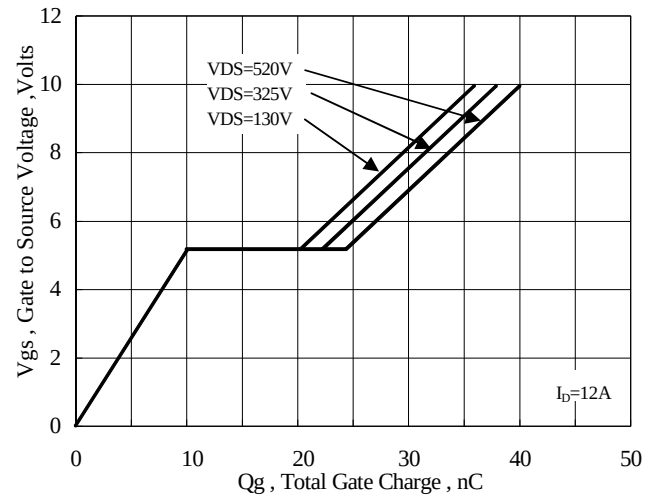


Figure 13 Typical Gate Charge vs Gate to Source Voltage



Test Circuit and Waveform

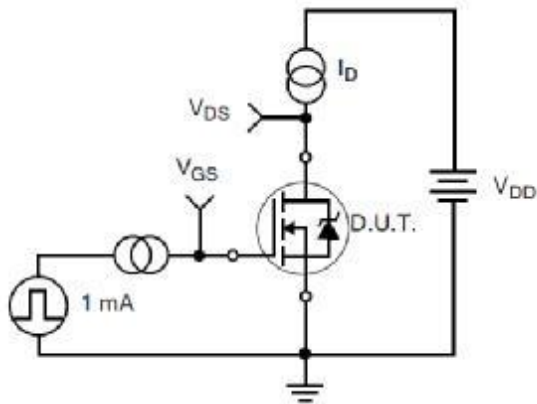


Figure 17. Gate Charge Test Circuit

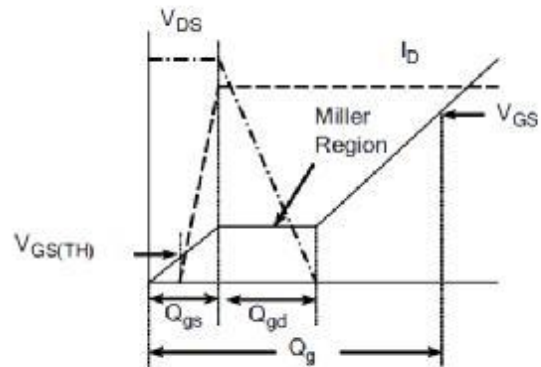


Figure 18. Gate Charge Waveform

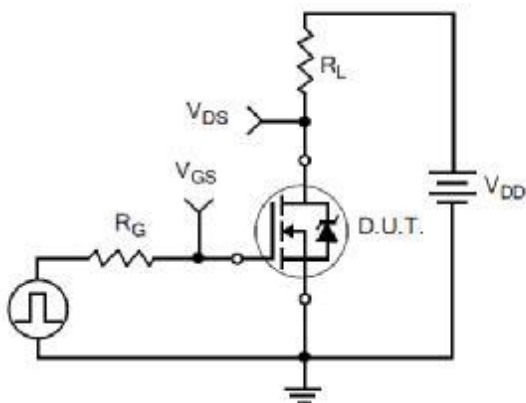


Figure 19. Resistive Switching Test Circuit

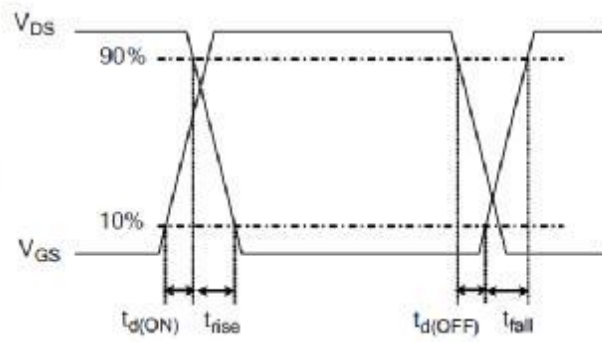


Figure 20. Resistive Switching Waveforms



HXY12N65F

Silicon N-Channel Power MOSFET

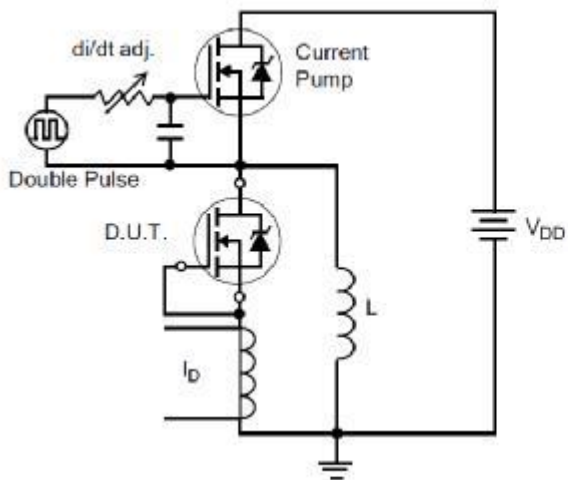


Figure 21. Diode Reverse Recovery Test Circuit

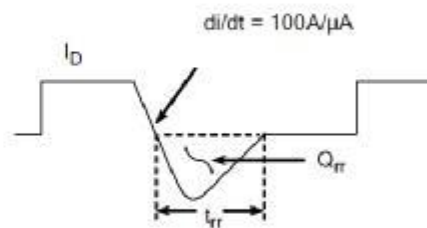


Figure 22. Diode Reverse Recovery Waveform

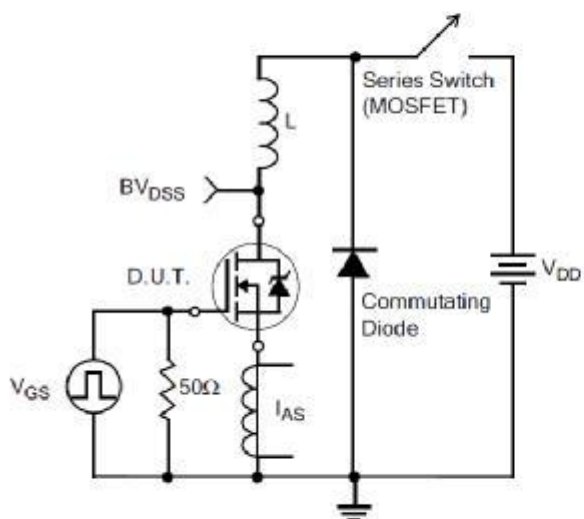


Figure 23. Unclamped Inductive Switching Test Circuit

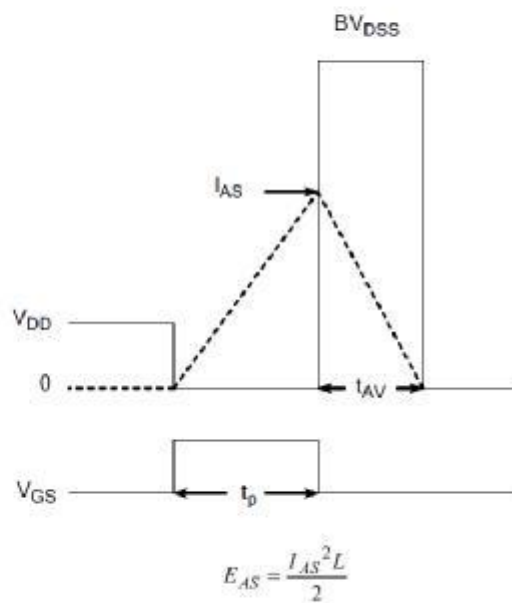
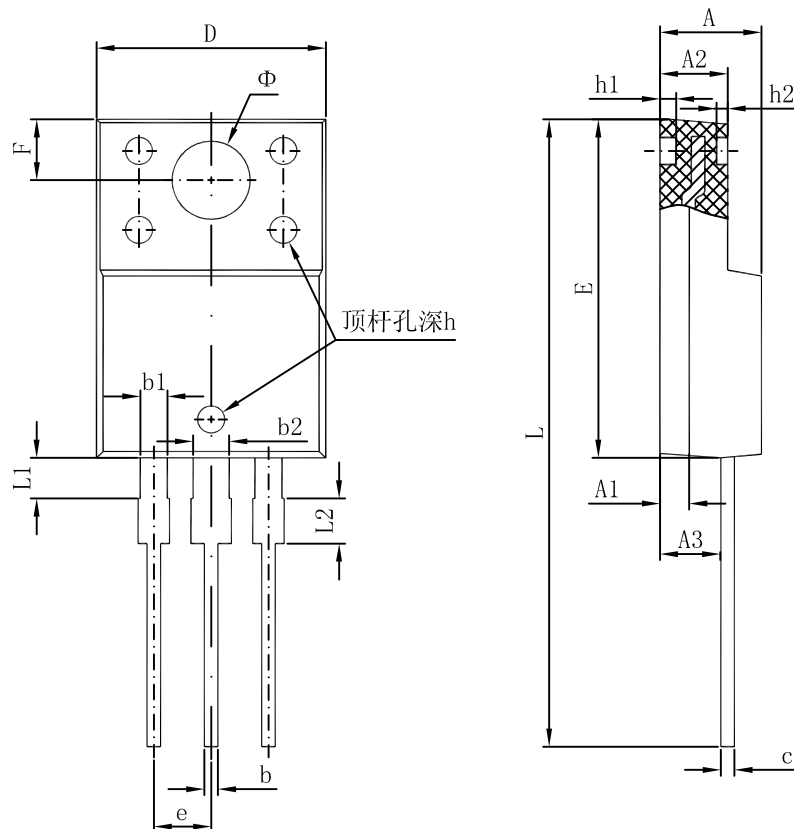


Figure 24. Unclamped Inductive Switching Waveforms



Package Information

TO-220F



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.300 REF.		0.051 REF.	
A2	2.800	3.200	0.110	0.126
A3	2.500	2.900	0.098	0.114
b	0.500	0.750	0.020	0.030
b1	1.100	1.350	0.043	0.053
b2	1.500	1.750	0.059	0.069
c	0.500	0.750	0.020	0.030
D	9.960	10.360	0.392	0.408
E	14.800	15.200	0.583	0.598
e	2.540 TYP.		0.100 TYP.	
F	2.700 REF.		0.106 REF.	
Φ	3.500 REF.		0.138 REF.	
h	0.000	0.300	0.000	0.012
h1	0.800 REF.		0.031 REF.	
h2	0.500 REF.		0.020 REF.	
L	28.000	28.400	1.102	1.118
L1	1.700	1.900	0.067	0.075
L2	1.900	2.100	0.075	0.083



Attention

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.